

**AMENDMENTS TO THE CLAIMS:**

Please amend the claims as follows:

1. (original) An improved p-type gallium nitride-based semiconductor device comprising:
  - a device structure that includes at least one p-type Group III nitride layer that includes some gallium;
  - a first silicon dioxide layer on said p-type layer;
  - a layer of a Group II metal source composition on said first SiO<sub>2</sub> layer; and
  - a second SiO<sub>2</sub> layer on said Group II metal source composition layer.
  
2. (original) A semiconductor device according to Claim 1 wherein said device structure comprises:
  - a conductive silicon carbide substrate;
  - a conductive buffer layer on said silicon carbide substrate for providing a crystal transition between said substrate and said Group III nitride portions of said device; and
  - an n-type Group III nitride layer on said buffer layer.
  
3. (original) A device according to Claim 1 wherein said first silicon dioxide layer is thick enough to create vacancies to a depth in said p-type layer that encourages atoms of said Group II metal to diffuse therein while still permitting diffusion from said Group II metal source composition through said first SiO<sub>2</sub> layer and into said p-type layer.
  
4. (original) A device according to Claim 1 wherein:
  - said first SiO<sub>2</sub> layer is about 1000 Å thick;
  - said Group II metal source composition layer is about 1000 Å thick; and
  - said second SiO<sub>2</sub> layer is about 2500 Å thick.

5. (original) A device according to Claim 1 wherein said Group III nitride comprises GaN and said source composition layer is selected from the group consisting of magnesium and zinc.

6. (withdrawn) A method of activating the p-type layers and passivating a Group III nitride device, the method comprising: thermally annealing the structure according to Claim 1.

7. (Currently amended) A device structure according to Claim ~~1~~ 2 wherein said substrate is n-type and has a carrier concentration of between about  $1 \times 10^{16} \text{ cm}^{-3}$  and about  $1 \times 10^{19} \text{ cm}^{-3}$ .

8. (original) A device according to Claim 1 wherein said Group II metal source composition layer comprises a Group II metal-containing compound.

9. (original) A device according to Claim 8 wherein said compound is selected from the group consisting of magnesium nitride and zinc phosphide.

10. (Currently amended) A device according to Claim 1 wherein said p-type gallium nitride layer has the formula  $\text{Ga}_x\text{Al}_y\text{In}_{1-x-y}\text{N}$  where  $0 < x \leq 1$  and  $0 \leq y \leq 1$ .

11. (original) A device according to Claim 1 comprising a plurality of silicon dioxide portions on said p-type Group III nitride layer, with a respective portion of said source composition on each said silicon dioxide portion.

12. (original) A device according to Claim 11 wherein said second silicon dioxide layer is limited to said source composition portions.

13. (original) A device according to Claim 11 wherein said second silicon dioxide portion covers said source composition portions and portions of said p-type Group III nitride layer.

14. (original) An improved p-type gallium nitride-based device comprising:  
a conductive silicon carbide substrate;  
a conductive buffer layer on said silicon carbide substrate for providing a crystal transition between said substrate and said GaN portions of said device;  
an n-type GaN layer on said buffer layer;  
a p-type GaN layer on said n-type layer;  
a first silicon dioxide layer on said p-type layer;  
a magnesium layer on said first SiO<sub>2</sub> layer for supplying p-type dopant to said p-type layer; and  
a second SiO<sub>2</sub> layer on said Mg layer for passivating said device;  
said first silicon dioxide layer being thick enough to create vacancies to a required depth in said p-GaN layer when said device is heated to temperatures between about 750° and 950° C while still permitting diffusion from the magnesium layer through said first SiO<sub>2</sub> layer and into the p-GaN layer at such temperatures.

15. (original) A device according to Claim 14 wherein said substrate is n-type.

16. (original) A device according to Claim 14 wherein said buffer is selected from the group consisting of: graded layers of Group III nitrides, homogeneous layers of Group III nitrides, heterogeneous layers of Group III nitrides and combinations thereof.

17. (original) A device according to Claim 14 wherein said n-type layer comprises Al<sub>x</sub>In<sub>y</sub>Ga<sub>1-x-y</sub>N where  $0 \leq x \leq 1$  and  $0 \leq y \leq 1$

18. (original) A device according to Claim 14 wherein said p-type layer comprises  $\text{Ga}_x\text{Al}_y\text{In}_{1-x-y}$  where  $0 < x \leq 1$  and  $0 \leq y \leq 1$ .

19. (withdrawn) A method of activating the p-type layers and passivating a Group III nitride device, the method comprising thermally annealing a structure that includes at least the following elements:

- at least one p-type Group III nitride layer that includes some gallium;
- a first silicon dioxide layer on said p-type layer;
- a layer of a Group II metal source composition on said first  $\text{SiO}_2$  layer; and
- a second  $\text{SiO}_2$  layer on said source composition layer layer.

20. (withdrawn) A method according to Claim 19 comprising annealing the structure for a time sufficient for the structure to reach at temperature of between about  $750^\circ$  and  $950^\circ$  C.

21. (withdrawn) A method according to Claim 20 comprising annealing the structure to reach a temperature of between about  $850^\circ$  and  $875^\circ$  C.

22. (withdrawn) A method according to Claim 20 comprising annealing the structure for about 5 minutes.

23. (withdrawn) A method of increasing the activation of a p-type Group III nitride layer that includes some GaN, the method comprising:

- forming a first layer of  $\text{SiO}_2$  on the p-type layer;
- forming a layer of a Group II metal source composition;
- forming a second layer of  $\text{SiO}_2$  on the metal layer; and
- annealing the structure to diffuse the metal from the metal layer into the p-type gallium-containing layer and to activate metal atoms in the p-type layer.

24. (withdrawn) A method according to Claim 23 wherein the step of forming the first SiO<sub>2</sub> layer comprises forming the SiO<sub>2</sub> layer to a thickness sufficient to create gallium vacancies to a required depth in said p-type layer during the annealing step while still permitting magnesium to diffuse from the metal layer through said first SiO<sub>2</sub> layer and into activated positions in the p-type layer.

25. (withdrawn) A method according to Claim 23 comprising annealing the structure at a temperature and for a time sufficient to provide an activated p-type layer of at least about 1E17.

26. (withdrawn) A method according to Claim 25 comprising forming the SiO<sub>2</sub> layer to a thickness of about 1000 Å and annealing the structure for a time sufficient for the structure to reach a temperature of between about 750° and 950° C.

27. (withdrawn) A method according to Claim 26 comprising annealing the structure to reach a temperature of between about 850° and 875° C.

28. (withdrawn) A method according to Claim 26 comprising annealing the structure for about 5 minutes.

29. (withdrawn) A method according to Claim 23 comprising increasing the activation of a p-type GaN layer.

30. (withdrawn) A method according to Claim 23 wherein the step of forming the source composition layer comprises forming a layer of a metal selected from the group consisting of magnesium and zinc on the first SiO<sub>2</sub> layer.

31. (withdrawn) A method according to Claim 23 wherein the step of forming the source composition layer comprises forming a layer of a compound containing a Group II metal on the first SiO<sub>2</sub> layer.

32. (withdrawn) A method according to Claim 31 comprising forming a layer of selected from the group consisting of magnesium nitride and zinc phosphide.

33. (withdrawn) A method according to Claim 23 and further comprising removing the first and second SiO<sub>2</sub> layers and the metal source composition layer and depositing a silicon nitride cap on the remaining structure.

34. (withdrawn) A method according to Claim 33 wherein the step of removing the layers comprises etching the layers.

35. (withdrawn) A method of creating a p-type layer from a nominally n-type GaN layer, the method comprising:

forming a first layer of SiO<sub>2</sub> on the nominally n-type layer;

forming a layer of magnesium on the first SiO<sub>2</sub> layer;

forming a second layer of SiO<sub>2</sub> on the magnesium layer; and

annealing the structure to diffuse magnesium from the magnesium layer into the nominally n-type GaN layer and to activate sufficient magnesium in the layer to produce p-type characteristics.

36. (withdrawn) A method according to Claim 35 comprising annealing the structure for a time sufficient for the structure to reach a temperature of between about 750° and 950° C.

37. (withdrawn) A method according to Claim 36 comprising annealing the structure to reach a temperature of between about 850° and 875° C.

38. (withdrawn) A method according to Claim 36 comprising annealing the structure for about 5 minutes.

39. (withdrawn) A method of creating a p-type layer from a nominal n-type GaN layer, the method comprising:

annealing the GaN layer in the presence of an adjacent SiO<sub>2</sub> layer, a layer of a Group II metal source composition on the adjacent SiO<sub>2</sub> layer and a second SiO<sub>2</sub> layer on the metal layer;

until the GaN layer demonstrates p-type characteristics.

40. (withdrawn) A method according to Claim 39 comprising annealing a GaN layer having a n-type carrier concentration of 5E16 or less

41. (withdrawn) A method according to Claim 39 comprising annealing the GaN layer until the GaN layer demonstrates a p-type carrier concentration of at least about 1E17.

42. (withdrawn) A method according to Claim 39 comprising annealing the structure for a time sufficient for the structure to reach a temperature of between about 750° and 950° C.

43. (withdrawn) A method according to Claim 42 comprising annealing the structure to reach a temperature of between about 850° and 875° C.

44. (withdrawn) A method according to Claim 42 comprising annealing the structure for about 5 minutes.